

### Features

- 18 dB Gain at 900 MHz
- 17 dBm P1dB at 900 MHz
- 30 dBm Output IP3 at 900 MHz
- 3.8 dB NF at 900 MHz
- MTTF > 100 Years
- Single Supply

### Description

The ASW101, a power amplifier MMIC, has a high linearity, high gain, and high efficiency over a wide range of frequency, being suitable for use in both receiver and transmitter of telecommunication systems up to 3 GHz. The amplifier is available in an SOT-89 package and passes through the stringent DC, RF, and reliability tests.



Package Style: SOT-89

### Typical Performance

Parameters	Units	Typical	
Frequency	MHz	900	2000
Gain	dB	18	11
S11	dB	-10	-10
S22	dB	-18	-18
Output IP3 <sup>1)</sup>	dBm	30	31
Noise Figure	dB	3.8	4.0
Output P1dB	dBm	17	18
Current	mA	40	40
Device Voltage	V	3.3	3.3

1) OIP3 is measured with two tones at an output power of +3 dBm/tone separated by 1 MHz.

### Application Circuit

- IF
- IF (Low Current)
- 500 ~ 2500 MHz

### Product Specifications

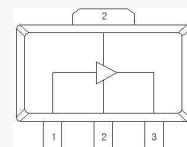
Parameters	Units	Min	Typ	Max
Testing Frequency	MHz		900	
Gain	dB	17	18	
S11	dB		-10	
S22	dB		-18	
Output IP3	dBm	29	30	
Noise Figure	dB		3.8	4.5
Output P1dB	dBm	16	17	
Current	mA	35	40	45
Device Voltage	V		3.3	

### Absolute Maximum Ratings

Parameters	Rating
Operating Case Temperature	-40 to +85°C
Storage Temperature	-40 to +150°C
Device Voltage	+6 V
Operating Junction Temperature	+150°C
Input RF Power (CW, 50ohm matched)*	25 dBm

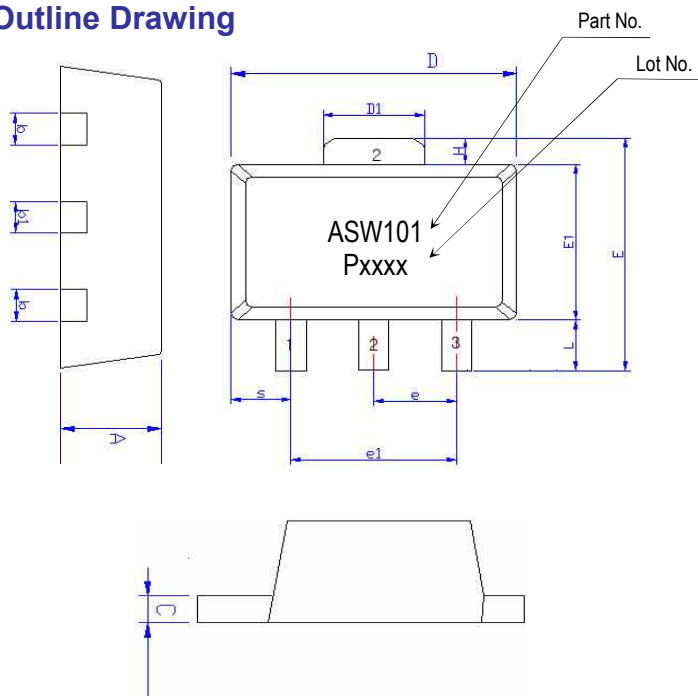
\* Please find the max. input power data from [http://www.asb.co.kr/pdf/Maximum\\_Input\\_Power\\_Analysis.pdf](http://www.asb.co.kr/pdf/Maximum_Input_Power_Analysis.pdf)

### Pin Configuration



Pin No.	Function
1	RF IN
2	GND
3	RF OUT / Bias

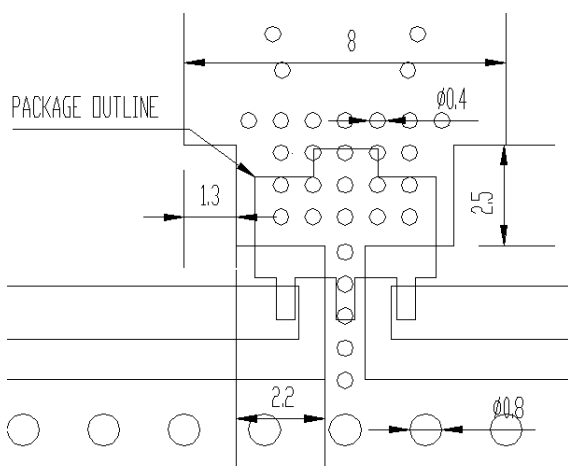
### Outline Drawing



Symbols	Dimensions (In mm)		
	MIN	NOM	MAX
A	1.40	1.50	1.60
L	0.89	1.04	1.20
b	0.36	0.42	0.48
b1	0.41	0.47	0.53
C	0.38	0.40	0.43
D	4.40	4.50	4.60
D1	1.40	1.60	1.75
E	3.64	---	4.25
E1	2.40	2.50	2.60
e1	2.90	3.00	3.10
H	0.35	0.40	0.45
S	0.65	0.75	0.85
e	1.40	1.50	1.60

Pin No.	Function
1	RF IN
2	GND
3	RF OUT / Bias

### Mounting Recommendation (in mm)



- Note:**
1. The number and size of ground via holes in a circuit board is critical for thermal and RF grounding considerations.
  2. We recommend that the ground via holes be placed on the bottom of the lead pin 2 and exposed pad of the device for better RF and thermal performance, as shown in the drawing at the left side.

### Ordering Information

Part Number	Description
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**APPLICATION CIRCUIT**

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**IF**

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**5 ~ 450 MHz**

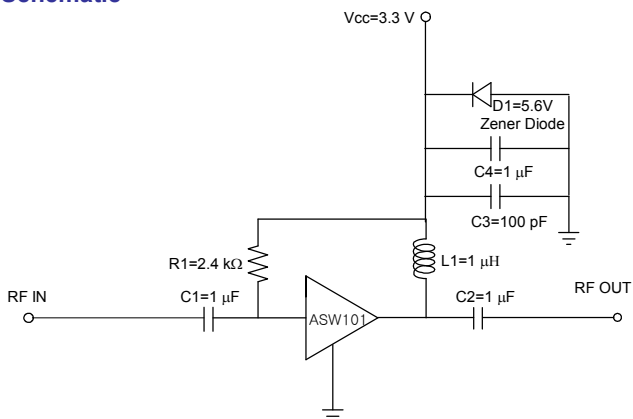
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**+3.3 V**

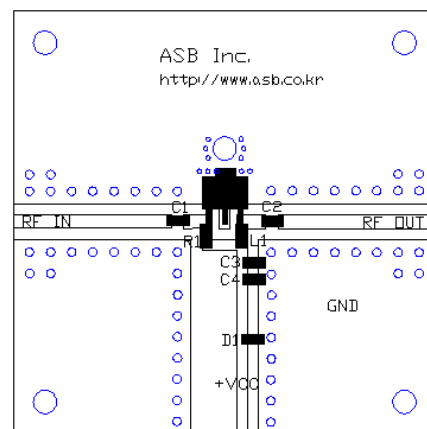
Frequency (MHz)	5	150	300	450
Magnitude S21 (dB)	25	24.5	23.5	21.5
Magnitude S11 (dB)	-15	-15	-14	-12
Magnitude S22 (dB)	-12	-15	-14	-12
Output P1dB (dBm)	17	17	17	17
Output IP3 <sup>1)</sup> (dBm)	28	29	30	30
Noise Figure (dB)	3.6	3.8	4.0	3.8
Device Voltage (V)	3.3			
Current (mA)	40			

1) OIP3 is measured with two tones at an output power of +3 dBm/tone separated by 1 MHz.

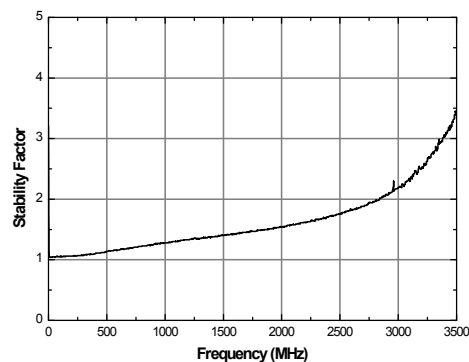
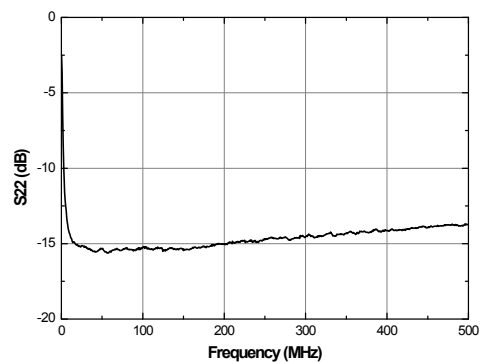
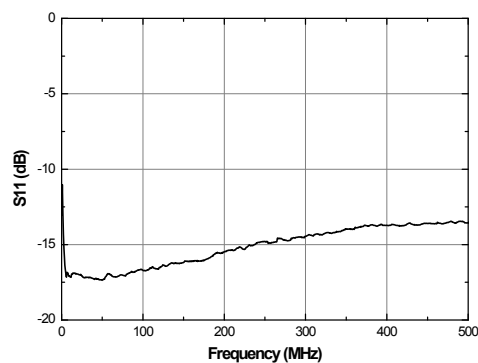
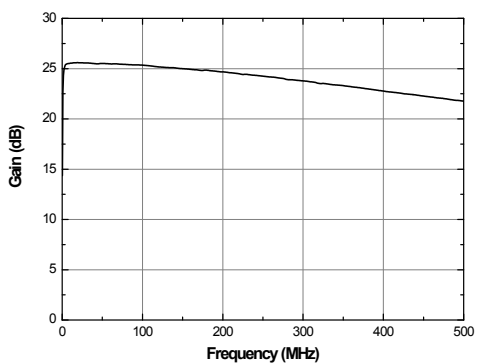
### Schematic



### Board Layout (FR4, 40x40 mm<sup>2</sup>, 0.8T)



### S-parameters & K-factor



### APPLICATION CIRCUIT

IF

Low Current

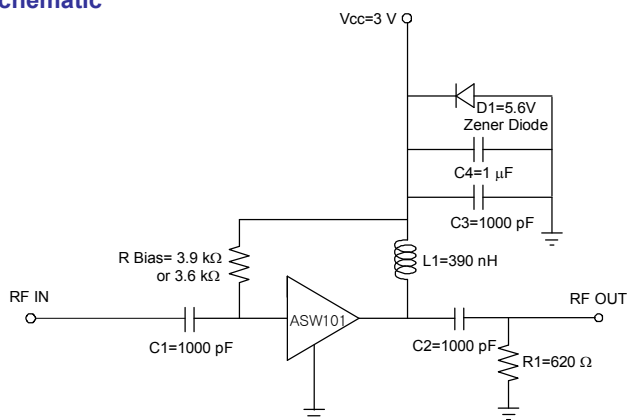
60 ~ 110 MHz

+3 V

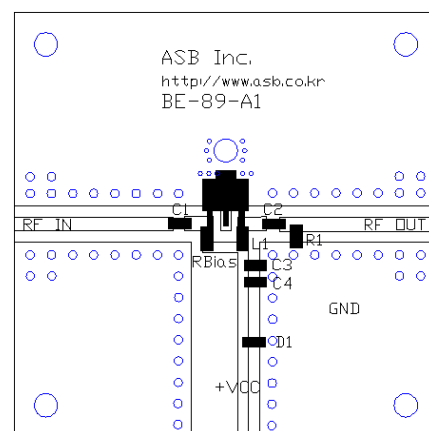
R Bias	3.9 kohm	3.6 kohm
Frequency (MHz)	60~110	60~110
Magnitude S21 (dB)	20	20.5
Gain Flatness (dB)	0.4	0.4
Magnitude S11 (dB)	-9.5	-10
Magnitude S22 (dB)	-9	-11
Output P1dB (dBm)	4.5	4.5
Output IP3 <sup>1)</sup> (dBm)	12	12
Noise Figure (dB)	2.4	2.4
Device Voltage (V)	3	3
Current (mA)	8	10

1) OIP3 is measured with two tones at an output power of -5 dBm/tone separated by 1 MHz.

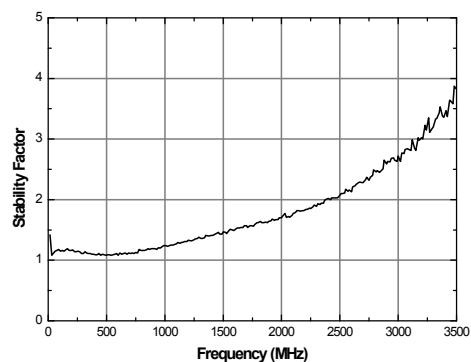
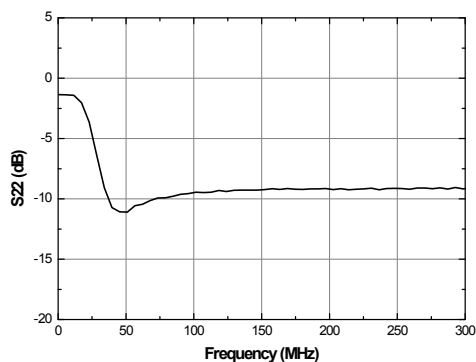
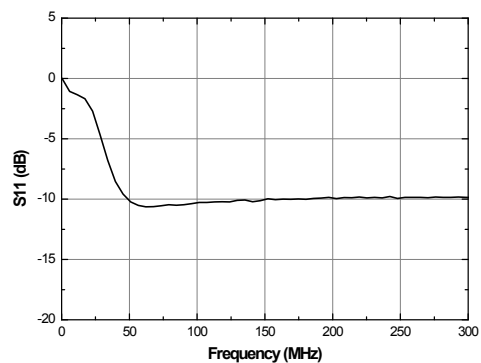
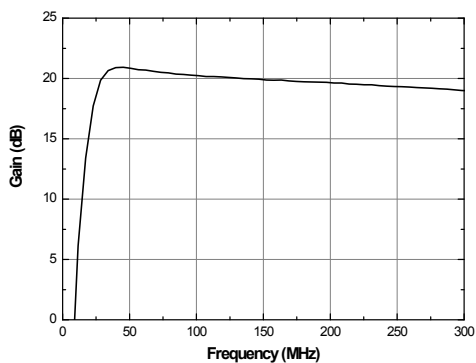
### Schematic



### Board Layout (FR4, 40x40 mm<sup>2</sup>, 0.8T)



### S-parameters (R Bias=3.9 kohm) & K-factor



**APPLICATION CIRCUIT**

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**500 ~ 2500 MHz**

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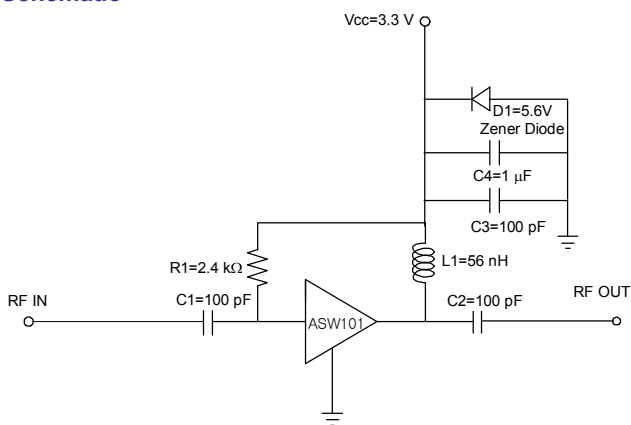
**+3.3 V**

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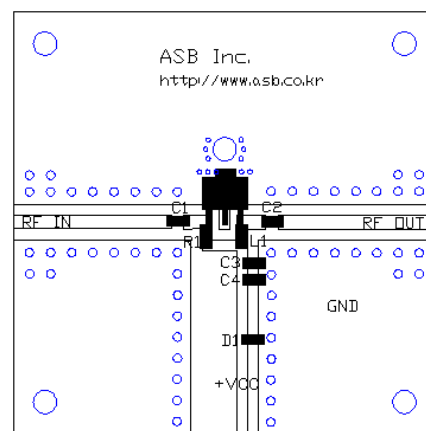
Frequency (MHz)	500	900	1750	2000	2400
Magnitude S21 (dB)	21	18	12.5	11	9.5
Magnitude S11 (dB)	-10	-10	-11	-10	-8.5
Magnitude S22 (dB)	-22	-18	-18	-18	-15
Output P1dB (dBm)	17	17	18	18	18
Output IP3 <sup>1)</sup> (dBm)	30	30	31	31	31
Noise Figure (dB)	4.2	3.8	3.9	4.0	4.5
Device Voltage (V)	3.3				
Current (mA)	40				

1) OIP3 is measured with two tones at an output power of +3 dBm/tone separated by 1 MHz.

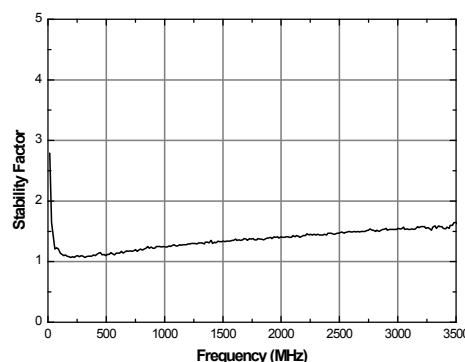
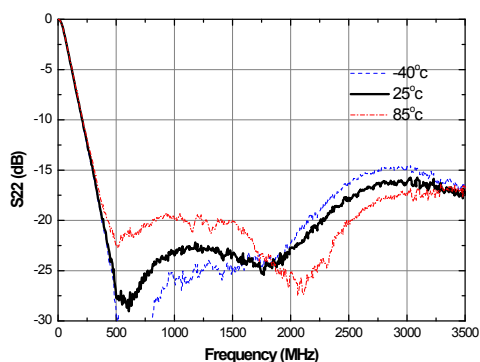
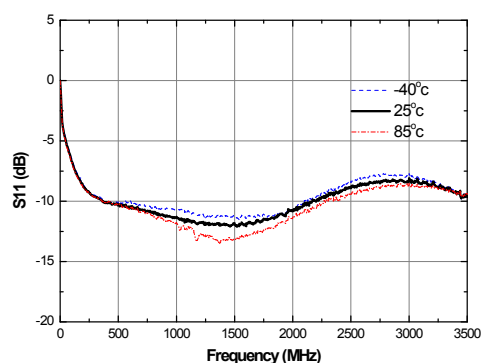
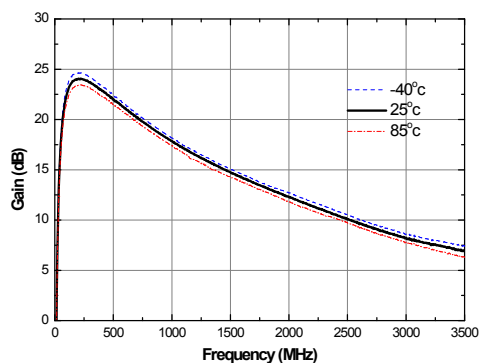
### Schematic



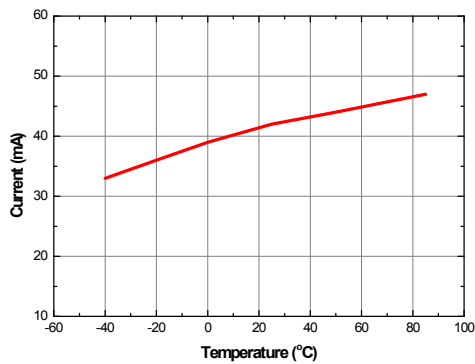
### Board Layout (FR4, 40x40 mm<sup>2</sup>, 0.8T)



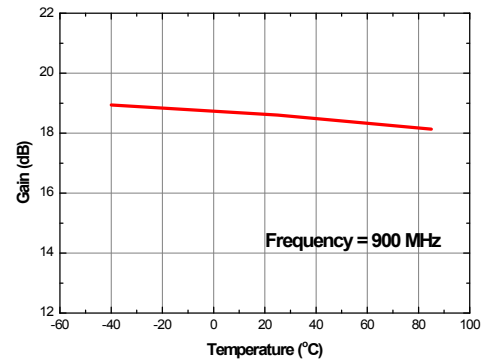
### S-parameters & K-factor



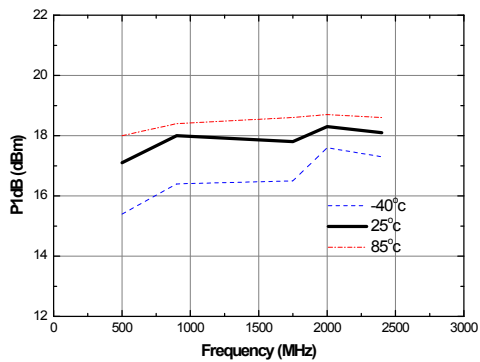
### Current vs. Temperature



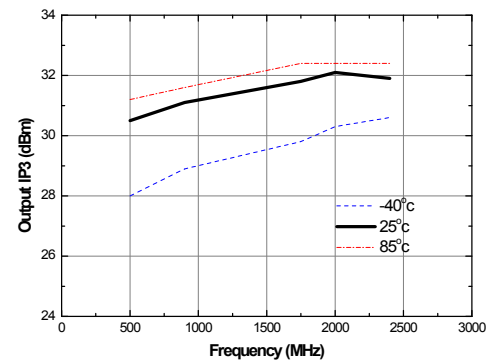
### Gain vs. Temperature



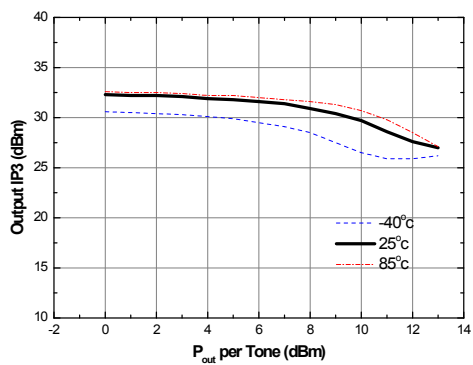
### P1dB vs. Frequency



### Output IP3 vs. Frequency



### Output IP3 vs. Tone Power (Frequency = 2000MHz)



### NF vs. Temperature (Frequency = 850MHz)

